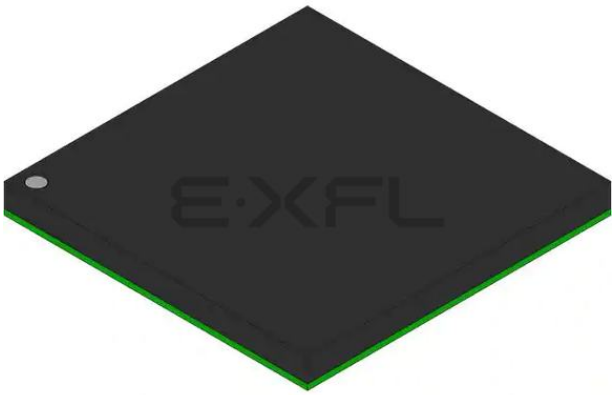

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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	-
Number of I/O	196
Number of Gates	-
Voltage - Supply	1.71V ~ 1.89V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	324-BGA
Supplier Device Package	324-FBGA (19x19)
Purchase URL	https://www.e-xfl.com/pro/item?MUrl=&PartUrl=ep20k60efc324-2x

Table 5. APEX 20K FineLine BGA Package Options & I/O Count *Notes (1), (2)*

Device	144 Pin	324 Pin	484 Pin	672 Pin	1,020 Pin
EP20K30E	93	128			
EP20K60E	93	196			
EP20K100		252			
EP20K100E	93	246			
EP20K160E			316		
EP20K200			382		
EP20K200E			376	376	
EP20K300E				408	
EP20K400				502 *(3)*	
EP20K400E				488 *(3)*	
EP20K600E				508 *(3)*	588
EP20K1000E				508 *(3)*	708
EP20K1500E					808

Notes to Tables 4 and 5:

(1) I/O counts include dedicated input and clock pins.

(2) APEX 20K device package types include thin quad flat pack (TQFP), plastic quad flat pack (PQFP), power quad flat pack (RQFP), 1.27-mm pitch ball-grid array (BGA), 1.00-mm pitch FineLine BGA, and pin-grid array (PGA) packages.

(3) This device uses a thermally enhanced package, which is taller than the regular package. Consult the *Altera Device Package Information Data Sheet* for detailed package size information.

Table 6. APEX 20K QFP, BGA & PGA Package Sizes

Feature	144-Pin TQFP	208-Pin QFP	240-Pin QFP	356-Pin BGA	652-Pin BGA	655-Pin PGA
Pitch (mm)	0.50	0.50	0.50	1.27	1.27	–
Area (mm^2)	484	924	1,218	1,225	2,025	3,906
Length × Width (mm × mm)	22 × 22	30.4 × 30.4	34.9 × 34.9	35 × 35	45 × 45	62.5 × 62.5

Table 7. APEX 20K FineLine BGA Package Sizes

Feature	144 Pin	324 Pin	484 Pin	672 Pin	1,020 Pin
Pitch (mm)	1.00	1.00	1.00	1.00	1.00
Area (mm^2)	169	361	529	729	1,089
Length × Width (mm × mm)	13 × 13	19 × 19	23 × 23	27 × 27	33 × 33

All APEX 20K devices are reconfigurable and are 100% tested prior to shipment. As a result, test vectors do not have to be generated for fault coverage purposes. Instead, the designer can focus on simulation and design verification. In addition, the designer does not need to manage inventories of different application-specific integrated circuit (ASIC) designs; APEX 20K devices can be configured on the board for the specific functionality required.

APEX 20K devices are configured at system power-up with data stored in an Altera serial configuration device or provided by a system controller. Altera offers in-system programmability (ISP)-capable EPC1, EPC2, and EPC16 configuration devices, which configure APEX 20K devices via a serial data stream. Moreover, APEX 20K devices contain an optimized interface that permits microprocessors to configure APEX 20K devices serially or in parallel, and synchronously or asynchronously. The interface also enables microprocessors to treat APEX 20K devices as memory and configure the device by writing to a virtual memory location, making reconfiguration easy.

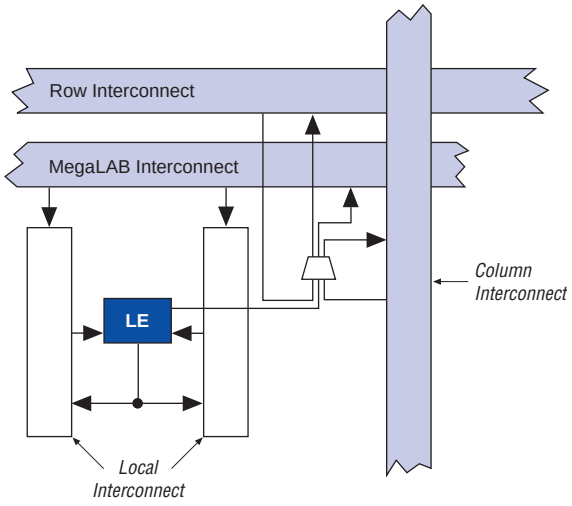
After an APEX 20K device has been configured, it can be reconfigured in-circuit by resetting the device and loading new data. Real-time changes can be made during system operation, enabling innovative reconfigurable computing applications.

APEX 20K devices are supported by the Altera Quartus II development system, a single, integrated package that offers HDL and schematic design entry, compilation and logic synthesis, full simulation and worst-case timing analysis, SignalTap logic analysis, and device configuration. The Quartus II software runs on Windows-based PCs, Sun SPARCstations, and HP 9000 Series 700/800 workstations.

The Quartus II software provides NativeLink interfaces to other industry-standard PC- and UNIX workstation-based EDA tools. For example, designers can invoke the Quartus II software from within third-party design tools. Further, the Quartus II software contains built-in optimized synthesis libraries; synthesis tools can use these libraries to optimize designs for APEX 20K devices. For example, the Synopsys Design Compiler library, supplied with the Quartus II development system, includes DesignWare functions optimized for the APEX 20K architecture.

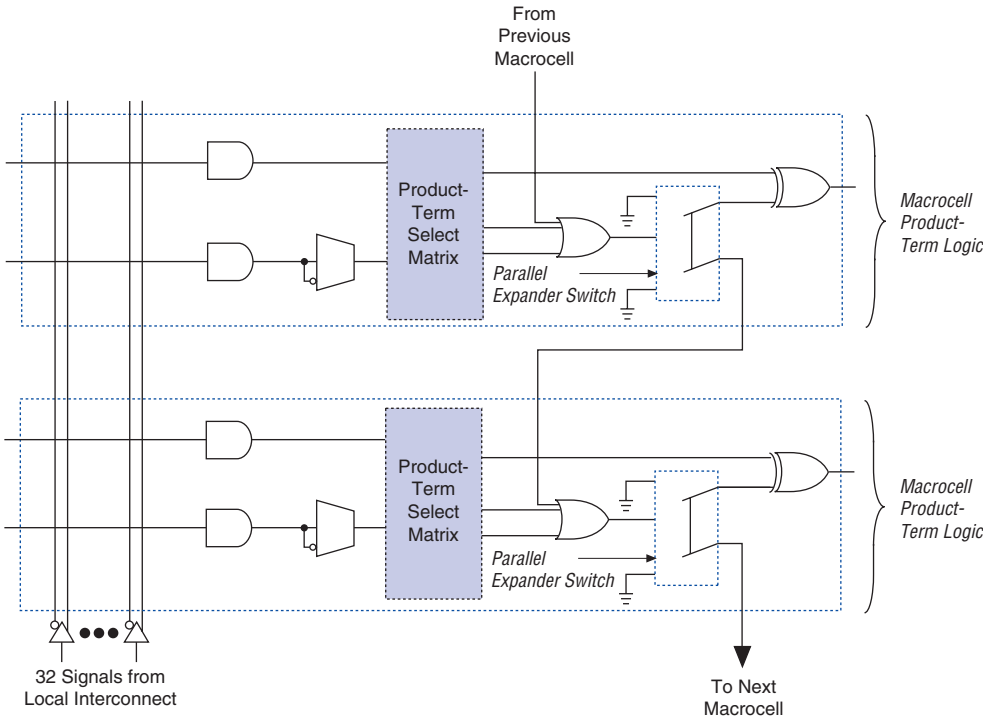
Figure 11 shows the intersection of a row and column interconnect, and how these forms of interconnects and LEs drive each other.

Figure 11. Driving the FastTrack Interconnect



APEX 20KE devices include an enhanced interconnect structure for faster routing of input signals with high fan-out. Column I/O pins can drive the FastRow™ interconnect, which routes signals directly into the local interconnect without having to drive through the MegaLAB interconnect. FastRow lines traverse two MegaLAB structures. Also, these pins can drive the local interconnect directly for fast setup times. On EP20K300E and larger devices, the FastRow interconnect drives the two MegaLABs in the top left corner, the two MegaLABs in the top right corner, the two MegaLABS in the bottom left corner, and the two MegaLABs in the bottom right corner. On EP20K200E and smaller devices, FastRow interconnect drives the two MegaLABs on the top and the two MegaLABs on the bottom of the device. On all devices, the FastRow interconnect drives all local interconnect in the appropriate MegaLABs except the local interconnect on the side of the MegaLAB opposite the ESB. Pins using the FastRow interconnect achieve a faster set-up time, as the signal does not need to use a MegaLAB interconnect line to reach the destination LE. Figure 12 shows the FastRow interconnect.

Figure 16. APEX 20K Parallel Expanders



Embedded System Block

The ESB can implement various types of memory blocks, including dual-port RAM, ROM, FIFO, and CAM blocks. The ESB includes input and output registers; the input registers synchronize writes, and the output registers can pipeline designs to improve system performance. The ESB offers a dual-port mode, which supports simultaneous reads and writes at two different clock frequencies. Figure 17 shows the ESB block diagram.

Figure 17. ESB Block Diagram

ESBs can implement synchronous RAM, which is easier to use than asynchronous RAM. A circuit using asynchronous RAM must generate the RAM write enable (WE) signal, while ensuring that its data and address signals meet setup and hold time specifications relative to the WE signal. In contrast, the ESB's synchronous RAM generates its own WE signal and is self-timed with respect to the global clock. Circuits using the ESB's self-timed RAM must only meet the setup and hold time specifications of the global clock.

ESB inputs are driven by the adjacent local interconnect, which in turn can be driven by the MegaLAB or FastTrack Interconnect. Because the ESB can be driven by the local interconnect, an adjacent LE can drive it directly for fast memory access. ESB outputs drive the MegaLAB and FastTrack Interconnect. In addition, ten ESB outputs, nine of which are unique output lines, drive the local interconnect for fast connection to adjacent LEs or for fast feedback product-term logic.

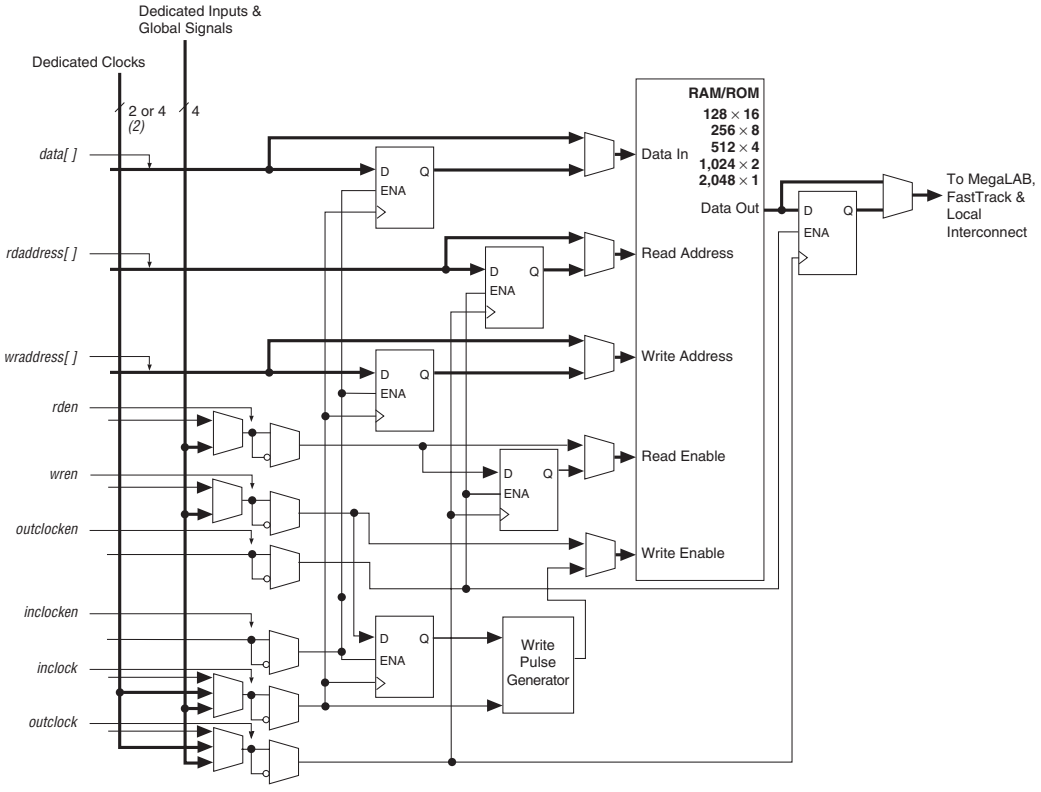
When implementing memory, each ESB can be configured in any of the following sizes: 128 × 16, 256 × 8, 512 × 4, 1,024 × 2, or 2,048 × 1. By combining multiple ESBs, the Quartus II software implements larger memory blocks automatically. For example, two 128 × 16 RAM blocks can be combined to form a 128 × 32 RAM block, and two 512 × 4 RAM blocks can be combined to form a 512 × 8 RAM block. Memory performance does not degrade for memory blocks up to 2,048 words deep. Each ESB can implement a 2,048-word-deep memory; the ESBs are used in parallel, eliminating the need for any external control logic and its associated delays.

To create a high-speed memory block that is more than 2,048 words deep, ESBs drive tri-state lines. Each tri-state line connects all ESBs in a column of MegaLAB structures, and drives the MegaLAB interconnect and row and column FastTrack Interconnect throughout the column. Each ESB incorporates a programmable decoder to activate the tri-state driver appropriately. For instance, to implement 8,192-word-deep memory, four ESBs are used. Eleven address lines drive the ESB memory, and two more drive the tri-state decoder. Depending on which 2,048-word memory page is selected, the appropriate ESB driver is turned on, driving the output to the tri-state line. The Quartus II software automatically combines ESBs with tri-state lines to form deeper memory blocks. The internal tri-state control logic is designed to avoid internal contention and floating lines. See Figure 18.

Read/Write Clock Mode

The read/write clock mode contains two clocks. One clock controls all registers associated with writing: data input, WE, and write address. The other clock controls all registers associated with reading: read enable (RE), read address, and data output. The ESB also supports clock enable and asynchronous clear signals; these signals also control the read and write registers independently. Read/write clock mode is commonly used for applications where reads and writes occur at different system frequencies. Figure 20 shows the ESB in read/write clock mode.

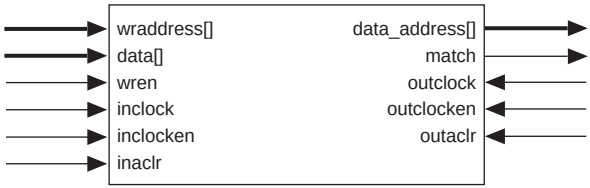
Figure 20. ESB in Read/Write Clock Mode *Note (1)*



Notes to Figure 20:

(1) All registers can be cleared asynchronously by ESB local interconnect signals, global signals, or the chip-wide reset.
(2) APEX 20KE devices have four dedicated clocks.

Figure 23. APEX 20KE CAM Block Diagram



CAM can be used in any application requiring high-speed searches, such as networking, communications, data compression, and cache management.

The APEX 20KE on-chip CAM provides faster system performance than traditional discrete CAM. Integrating CAM and logic into the APEX 20KE device eliminates off-chip and on-chip delays, improving system performance.

When in CAM mode, the ESB implements 32-word, 32-bit CAM. Wider or deeper CAM can be implemented by combining multiple CAMs with some ancillary logic implemented in LEs. The Quartus II software combines ESBs and LEs automatically to create larger CAMs.

CAM supports writing "don't care" bits into words of the memory. The "don't-care" bit can be used as a mask for CAM comparisons; any bit set to "don't-care" has no effect on matches.

The output of the CAM can be encoded or unencoded. When encoded, the ESB outputs an encoded address of the data's location. For instance, if the data is located in address `12`, the ESB output is `12`. When unencoded, the ESB uses its 16 outputs to show the location of the data over two clock cycles. In this case, if the data is located in address `12`, the 12th output line goes high. When using unencoded outputs, two clock cycles are required to read the output because a 16-bit output bus is used to show the status of 32 words.

The encoded output is better suited for designs that ensure duplicate data is not written into the CAM. If duplicate data is written into two locations, the CAM's output will be incorrect. If the CAM may contain duplicate data, the unencoded output is a better solution; CAM with unencoded outputs can distinguish multiple data locations.

CAM can be pre-loaded with data during configuration, or it can be written during system operation. In most cases, two clock cycles are required to write each word into CAM. When "don't-care" bits are used, a third clock cycle is required.

Table 18. APEX 20KE Clock Input & Output Parameters (Part 1 of 2) *Note (1)*

Symbol	Parameter	I/O Standard	-1X Speed Grade		-2X Speed Grade		Units
			Min	Max	Min	Max	
f_{VCO} *(4)*	Voltage controlled oscillator operating range		200	500	200	500	MHz
f_{CLOCK0}	`Clock0` PLL output frequency for internal use		1.5	335	1.5	200	MHz
f_{CLOCK1}	`Clock1` PLL output frequency for internal use		20	335	20	200	MHz
f_{CLOCK0_EXT}	Output clock frequency for external `clock0` output	3.3-V LVTTL	1.5	245	1.5	226	MHz
		2.5-V LVTTL	1.5	234	1.5	221	MHz
		1.8-V LVTTL	1.5	223	1.5	216	MHz
		GTL+	1.5	205	1.5	193	MHz
		SSTL-2 Class I	1.5	158	1.5	157	MHz
		SSTL-2 Class II	1.5	142	1.5	142	MHz
		SSTL-3 Class I	1.5	166	1.5	162	MHz
		SSTL-3 Class II	1.5	149	1.5	146	MHz
		LVDS	1.5	420	1.5	350	MHz
f_{CLOCK1_EXT}	Output clock frequency for external `clock1` output	3.3-V LVTTL	20	245	20	226	MHz
		2.5-V LVTTL	20	234	20	221	MHz
		1.8-V LVTTL	20	223	20	216	MHz
		GTL+	20	205	20	193	MHz
		SSTL-2 Class I	20	158	20	157	MHz
		SSTL-2 Class II	20	142	20	142	MHz
		SSTL-3 Class I	20	166	20	162	MHz
		SSTL-3 Class II	20	149	20	146	MHz
		LVDS	20	420	20	350	MHz

Table 25. APEX 20K 5.0-V Tolerant Device DC Operating Conditions (Part 2 of 2) *Notes (2), (7), (8)*

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{OL}	3.3-V low-level TTL output voltage	I_{OL} = 12 mA DC, V_{CCIO} = 3.00 V *(11)*			0.45	V
	3.3-V low-level CMOS output voltage	I_{OL} = 0.1 mA DC, V_{CCIO} = 3.00 V *(11)*			0.2	V
	3.3-V low-level PCI output voltage	I_{OL} = 1.5 mA DC, V_{CCIO} = 3.00 to 3.60 V *(11)*			$0.1 \times V_{CCIO}$	V
	2.5-V low-level output voltage	I_{OL} = 0.1 mA DC, V_{CCIO} = 2.30 V *(11)*			0.2	V
		I_{OL} = 1 mA DC, V_{CCIO} = 2.30 V *(11)*			0.4	V
		I_{OL} = 2 mA DC, V_{CCIO} = 2.30 V *(11)*			0.7	V
I_I	Input pin leakage current	V_I = 5.75 to –0.5 V	–10		10	µA
I_{OZ}	Tri-stated I/O pin leakage current	V_O = 5.75 to –0.5 V	–10		10	µA
I_{CC0}	V_{CC} supply current (standby) (All ESBs in power-down mode)	V_I = ground, no load, no toggling inputs, -1 speed grade *(12)*		10		mA
		V_I = ground, no load, no toggling inputs, -2, -3 speed grades *(12)*		5		mA
R_{CONF}	Value of I/O pin pull-up resistor before and during configuration	V_{CCIO} = 3.0 V *(13)*	20		50	W
		V_{CCIO} = 2.375 V *(13)*	30		80	W

Table 26. APEX 20K 5.0-V Tolerant Device Capacitance *Notes (2), (14)*

Symbol	Parameter	Conditions	Min	Max	Unit
C_{IN}	Input capacitance	V_{IN} = 0 V, f = 1.0 MHz		8	pF
C_{INCLK}	Input capacitance on dedicated clock pin	V_{IN} = 0 V, f = 1.0 MHz		12	pF
C_{OUT}	Output capacitance	V_{OUT} = 0 V, f = 1.0 MHz		8	pF

Notes to Tables 23 through 26:

(1) See the *Operating Requirements for Altera Devices Data Sheet*.
(2) All APEX 20K devices are 5.0-V tolerant.
(3) Minimum DC input is –0.5 V. During transitions, the inputs may undershoot to –2.0 V or overshoot to 5.75 V for input currents less than 100 mA and periods shorter than 20 ns.
(4) Numbers in parentheses are for industrial-temperature-range devices.
(5) Maximum V_{CC} rise time is 100 ms, and V_{CC} must rise monotonically.
(6) All pins, including dedicated inputs, clock I/O, and JTAG pins, may be driven before V_{CCINT} and V_{CCIO} are powered.
(7) Typical values are for T_A = 25° C, V_{CCINT} = 2.5 V, and V_{CCIO} = 2.5 or 3.3 V.
(8) These values are specified in the APEX 20K device recommended operating conditions, shown in Table 26 on page 62.
(9) The APEX 20K input buffers are compatible with 2.5-V and 3.3-V (LVTTL and LVCMOS) signals. Additionally, the input buffers are 3.3-V PCI compliant when V_{CCIO} and V_{CCINT} meet the relationship shown in Figure 33 on page 68.
(10) The I_{OH} parameter refers to high-level TTL, PCI or CMOS output current.
(11) The I_{OL} parameter refers to low-level TTL, PCI, or CMOS output current. This parameter applies to open-drain pins as well as output pins.
(12) This value is specified for normal device operation. The value may vary during power-up.
(13) Pin pull-up resistance values will be lower if an external source drives the pin higher than V_{CCIO}.
(14) Capacitance is sample-tested only.

Tables 27 through 30 provide information on absolute maximum ratings, recommended operating conditions, DC operating conditions, and capacitance for 1.8-V APEX 20KE devices.

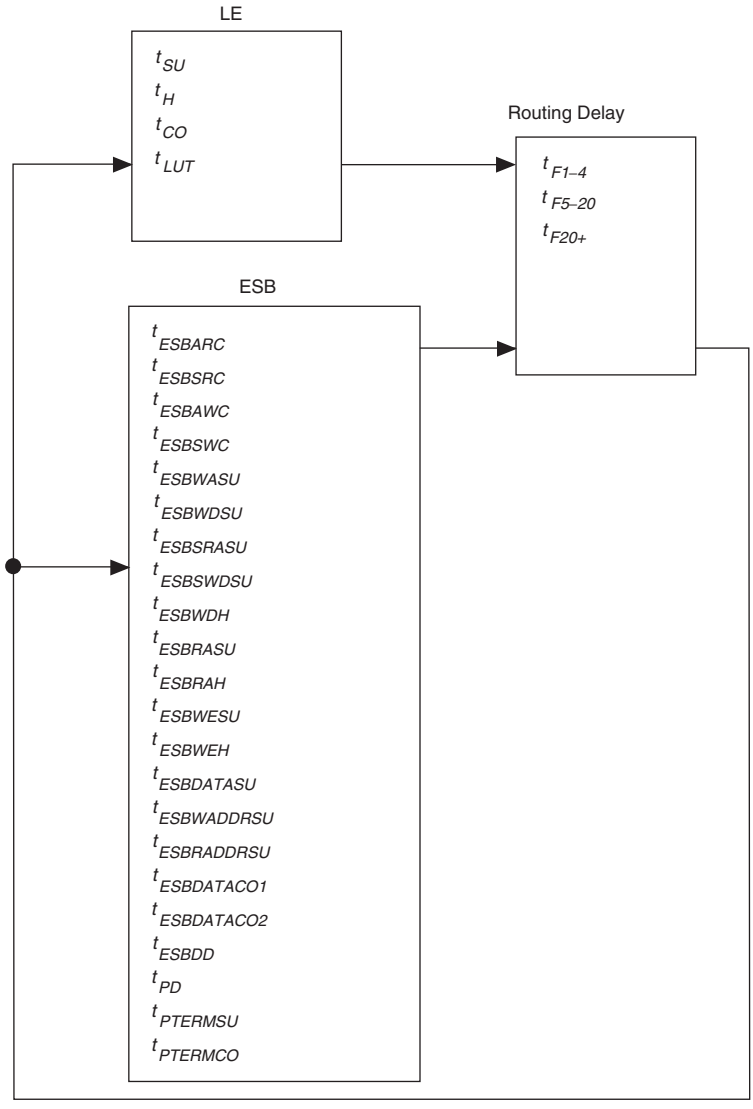
Table 27. APEX 20KE Device Absolute Maximum Ratings *Note (1)*

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CCINT}	Supply voltage	With respect to ground *(2)*	–0.5	2.5	V
V_{CCIO}			–0.5	4.6	V
V_I	DC input voltage		–0.5	4.6	V
I_{OUT}	DC output current, per pin		–25	25	mA
T_{STG}	Storage temperature	No bias	–65	150	° C
T_{AMB}	Ambient temperature	Under bias	–65	135	° C
T_J	Junction temperature	PQFP, RQFP, TQFP, and BGA packages, under bias		135	° C
		Ceramic PGA packages, under bias		150	° C

Table 29. APEX 20KE Device DC Operating Conditions *Notes (7), (8), (9)*

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{IH}	High-level LVTTL, CMOS, or 3.3-V PCI input voltage		1.7, 0.5 × V_{CCIO} *(10)*		4.1	V
V_{IL}	Low-level LVTTL, CMOS, or 3.3-V PCI input voltage		–0.5		0.8, 0.3 × V_{CCIO} *(10)*	V
V_{OH}	3.3-V high-level LVTTL output voltage	I_{OH} = –12 mA DC, V_{CCIO} = 3.00 V *(11)*	2.4			V
	3.3-V high-level LVCMOS output voltage	I_{OH} = –0.1 mA DC, V_{CCIO} = 3.00 V *(11)*	V_{CCIO} – 0.2			V
	3.3-V high-level PCI output voltage	I_{OH} = –0.5 mA DC, V_{CCIO} = 3.00 to 3.60 V *(11)*	0.9 × V_{CCIO}			V
	2.5-V high-level output voltage	I_{OH} = –0.1 mA DC, V_{CCIO} = 2.30 V *(11)*	2.1			V
		I_{OH} = –1 mA DC, V_{CCIO} = 2.30 V *(11)*	2.0			V
		I_{OH} = –2 mA DC, V_{CCIO} = 2.30 V *(11)*	1.7			V
V_{OL}	3.3-V low-level LVTTL output voltage	I_{OL} = 12 mA DC, V_{CCIO} = 3.00 V *(12)*			0.4	V
	3.3-V low-level LVCMOS output voltage	I_{OL} = 0.1 mA DC, V_{CCIO} = 3.00 V *(12)*			0.2	V
	3.3-V low-level PCI output voltage	I_{OL} = 1.5 mA DC, V_{CCIO} = 3.00 to 3.60 V *(12)*			0.1 × V_{CCIO}	V
	2.5-V low-level output voltage	I_{OL} = 0.1 mA DC, V_{CCIO} = 2.30 V *(12)*			0.2	V
		I_{OL} = 1 mA DC, V_{CCIO} = 2.30 V *(12)*			0.4	V
		I_{OL} = 2 mA DC, V_{CCIO} = 2.30 V *(12)*			0.7	V
I_I	Input pin leakage current	V_I = 4.1 to –0.5 V *(13)*	–10		10	µA
I_{OZ}	Tri-stated I/O pin leakage current	V_O = 4.1 to –0.5 V *(13)*	–10		10	µA
I_{CC0}	V_{CC} supply current (standby) (All ESBs in power-down mode)	V_I = ground, no load, no toggling inputs, -1 speed grade		10		mA
		V_I = ground, no load, no toggling inputs, -2, -3 speed grades		5		mA
R_{CONF}	Value of I/O pin pull-up resistor before and during configuration	V_{CCIO} = 3.0 V *(14)*	20		50	kΩ
		V_{CCIO} = 2.375 V *(14)*	30		80	kΩ
		V_{CCIO} = 1.71 V *(14)*	60		150	kΩ

Figure 37. APEX 20KE f_{MAX} Timing Model



Note to Tables 32 and 33:
(1) These timing parameters are sample-tested only.

Tables 34 through 37 show APEX 20KE LE, ESB, routing, and functional timing microparameters for the f_{MAX} timing model.

Table 34. APEX 20KE LE Timing Microparameters

Symbol	Parameter
t_{SU}	LE register setup time before clock
t_{H}	LE register hold time after clock
t_{CO}	LE register clock-to-output delay
t_{LUT}	LUT delay for data-in to data-out

Table 35. APEX 20KE ESB Timing Microparameters

Symbol	Parameter
t_{ESBARC}	ESB Asynchronous read cycle time
t_{ESBSRC}	ESB Synchronous read cycle time
t_{ESBAWC}	ESB Asynchronous write cycle time
t_{ESBSWC}	ESB Synchronous write cycle time
$t_{ESBWASU}$	ESB write address setup time with respect to WE
t_{ESBWAH}	ESB write address hold time with respect to WE
$t_{ESBWDSU}$	ESB data setup time with respect to WE
t_{ESBWDH}	ESB data hold time with respect to WE
$t_{ESBRASU}$	ESB read address setup time with respect to RE
t_{ESBRAH}	ESB read address hold time with respect to RE
$t_{ESBWESU}$	ESB WE setup time before clock when using input register
t_{ESBWEH}	ESB WE hold time after clock when using input register
$t_{ESBDATASU}$	ESB data setup time before clock when using input register
$t_{ESBDATAH}$	ESB data hold time after clock when using input register
$t_{ESBWADDRSU}$	ESB write address setup time before clock when using input registers
$t_{ESBRADDRSU}$	ESB read address setup time before clock when using input registers
$t_{ESBDATACO1}$	ESB clock-to-output delay when using output registers
$t_{ESBDATACO2}$	ESB clock-to-output delay without output registers
t_{ESBDD}	ESB data-in to data-out delay for RAM mode
t_{PD}	ESB Macrocell input to non-registered output
$t_{PTERMSU}$	ESB Macrocell register setup time before clock
$t_{PTERMCO}$	ESB Macrocell register clock-to-output delay

Tables 40 through 42 show the f_{MAX} timing parameters for EP20K100, EP20K200, and EP20K400 APEX 20K devices.

Table 40. EP20K100 f_{MAX} Timing Parameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Units
	Min	Max	Min	Max	Min	Max	
t_{SU}	0.5		0.6		0.8		ns
t_{H}	0.7		0.8		1.0		ns
t_{CO}		0.3		0.4		0.5	ns
t_{LUT}		0.8		1.0		1.3	ns
t_{ESBRC}		1.7		2.1		2.4	ns
t_{ESBWC}		5.7		6.9		8.1	ns
$t_{ESBWESU}$	3.3		3.9		4.6		ns
$t_{ESBDATASU}$	2.2		2.7		3.1		ns
$t_{ESBDATAH}$	0.6		0.8		0.9		ns
$t_{ESBADDRSU}$	2.4		2.9		3.3		ns
$t_{ESBDATACO1}$		1.3		1.6		1.8	ns
$t_{ESBDATACO2}$		2.6		3.1		3.6	ns
t_{ESBDD}		2.5		3.3		3.6	ns
t_{PD}		2.5		3.0		3.6	ns
$t_{PTERMSU}$	2.3		2.6		3.2		ns
$t_{PTERMCO}$		1.5		1.8		2.1	ns
t_{F1-4}		0.5		0.6		0.7	ns
t_{F5-20}		1.6		1.7		1.8	ns
t_{F20+}		2.2		2.2		2.3	ns
t_{CH}	2.0		2.5		3.0		ns
t_{CL}	2.0		2.5		3.0		ns
t_{CLRP}	0.3		0.4		0.4		ns
t_{PREP}	0.5		0.5		0.5		ns
t_{ESBCH}	2.0		2.5		3.0		ns
t_{ESBCL}	2.0		2.5		3.0		ns
t_{ESBWP}	1.6		1.9		2.2		ns
t_{ESBRP}	1.0		1.3		1.4		ns

Table 52. EP20K30E Minimum Pulse Width Timing Parameters

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t_{CH}	0.55		0.78		1.15		ns
t_{CL}	0.55		0.78		1.15		ns
t_{CLRP}	0.22		0.31		0.46		ns
t_{PREP}	0.22		0.31		0.46		ns
t_{ESBCH}	0.55		0.78		1.15		ns
t_{ESBCL}	0.55		0.78		1.15		ns
t_{ESBWP}	1.43		2.01		2.97		ns
t_{ESBRP}	1.15		1.62		2.39		ns

Table 53. EP20K30E External Timing Parameters

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t_{INSU}	2.02		2.13		2.24		ns
t_{INH}	0.00		0.00		0.00		ns
t_{OUTCO}	2.00	4.88	2.00	5.36	2.00	5.88	ns
$t_{INSUPLL}$	2.11		2.23		-		ns
t_{INHPLL}	0.00		0.00		-		ns
$t_{OUTCOPLL}$	0.50	2.60	0.50	2.88	-	-	ns

Table 54. EP20K30E External Bidirectional Timing Parameters

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
$t_{INSUBIDIR}$	1.85		1.77		1.54		ns
$t_{INHBIDIR}$	0.00		0.00		0.00		ns
$t_{OUTCOBIDIR}$	2.00	4.88	2.00	5.36	2.00	5.88	ns
$t_{XZBIDIR}$		7.48		8.46		9.83	ns
$t_{ZXBIDIR}$		7.48		8.46		9.83	ns
$t_{INSUBIDIRPLL}$	4.12		4.24		-		ns
$t_{INHBIDIRPLL}$	0.00		0.00		-		ns
$t_{OUTCOBIDIRPLL}$	0.50	2.60	0.50	2.88	-	-	ns
$t_{XZBIDIRPLL}$		5.21		5.99		-	ns
$t_{ZXBIDIRPLL}$		5.21		5.99		-	ns

Table 76. EP20K200E Minimum Pulse Width Timing Parameters

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t_{CH}	1.36		2.44		2.65		ns
t_{CL}	1.36		2.44		2.65		ns
t_{CLRP}	0.18		0.19		0.21		ns
t_{PREP}	0.18		0.19		0.21		ns
t_{ESBCH}	1.36		2.44		2.65		ns
t_{ESBCL}	1.36		2.44		2.65		ns
t_{ESBWP}	1.18		1.48		1.76		ns
t_{ESBRP}	0.95		1.17		1.41		ns

Table 77. EP20K200E External Timing Parameters

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t_{INSU}	2.24		2.35		2.47		ns
t_{INH}	0.00		0.00		0.00		ns
t_{OUTCO}	2.00	5.12	2.00	5.62	2.00	6.11	ns
$t_{INSUPLL}$	2.13		2.07		-		ns
t_{INHPLL}	0.00		0.00		-		ns
$t_{OUTCOPLL}$	0.50	3.01	0.50	3.36	-	-	ns

Table 78. EP20K200E External Bidirectional Timing Parameters

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
$t_{INSUBIDIR}$	2.81		3.19		3.54		ns
$t_{INHBIDIR}$	0.00		0.00		0.00		ns
$t_{OUTCOBIDIR}$	2.00	5.12	2.00	5.62	2.00	6.11	ns
$t_{XZBIDIR}$		7.51		8.32		8.67	ns
$t_{ZXBIDIR}$		7.51		8.32		8.67	ns
$t_{INSUBIDIRPLL}$	3.30		3.64		-		ns
$t_{INHBIDIRPLL}$	0.00		0.00		-		ns
$t_{OUTCOBIDIRPLL}$	0.50	3.01	0.50	3.36	-	-	ns
$t_{XZBIDIRPLL}$		5.40		6.05		-	ns
$t_{ZXBIDIRPLL}$		5.40		6.05		-	ns

Tables 79 through 84 describe f_{MAX} LE Timing Microparameters, f_{MAX} ESB Timing Microparameters, f_{MAX} Routing Delays, Minimum Pulse Width Timing Parameters, External Timing Parameters, and External Bidirectional Timing Parameters for EP20K300E APEX 20KE devices.

Table 79. EP20K300E f_{MAX} LE Timing Microparameters

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t_{SU}	0.16		0.17		0.18		ns
t_{H}	0.31		0.33		0.38		ns
t_{CO}		0.28		0.38		0.51	ns
t_{LUT}		0.79		1.07		1.43	ns

Table 87. EP20K400E f_{MAX} Routing Delays

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{F1-4}		0.25		0.25		0.26	ns
t_{F5-20}		1.01		1.12		1.25	ns
t_{F20+}		3.71		3.92		4.17	ns

Table 88. EP20K400E Minimum Pulse Width Timing Parameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{CH}	1.36		2.22		2.35		ns
t_{CL}	1.36		2.26		2.35		ns
t_{CLRP}	0.18		0.18		0.19		ns
t_{PREP}	0.18		0.18		0.19		ns
t_{ESBCH}	1.36		2.26		2.35		ns
t_{ESBCL}	1.36		2.26		2.35		ns
t_{ESBWP}	1.17		1.38		1.56		ns
t_{ESBRP}	0.94		1.09		1.25		ns

Table 89. EP20K400E External Timing Parameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{INSU}	2.51		2.64		2.77		ns
t_{INH}	0.00		0.00		0.00		ns
t_{OUTCO}	2.00	5.25	2.00	5.79	2.00	6.32	ns
$t_{INSUPLL}$	3.221		3.38		-		ns
t_{INHPLL}	0.00		0.00		-		ns
$t_{OUTCOPLL}$	0.50	2.25	0.50	2.45	-	-	ns

Table 99. EP20K1000E f_{MAX} Routing Delays

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{F1-4}		0.27		0.27		0.27	ns
t_{F5-20}		1.45		1.63		1.75	ns
t_{F20+}		4.15		4.33		4.97	ns

Table 100. EP20K1000E Minimum Pulse Width Timing Parameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{CH}	1.25		1.43		1.67		ns
t_{CL}	1.25		1.43		1.67		ns
t_{CLRP}	0.20		0.20		0.20		ns
t_{PREP}	0.20		0.20		0.20		ns
t_{ESBCH}	1.25		1.43		1.67		ns
t_{ESBCL}	1.25		1.43		1.67		ns
t_{ESBWP}	1.28		1.51		1.65		ns
t_{ESBRP}	1.11		1.29		1.41		ns

Table 101. EP20K1000E External Timing Parameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{INSU}	2.70		2.84		2.97		ns
t_{INH}	0.00		0.00		0.00		ns
t_{OUTCO}	2.00	5.75	2.00	6.33	2.00	6.90	ns
$t_{INSUPLL}$	1.64		2.09		-		ns
t_{INHPLL}	0.00		0.00		-		ns
$t_{OUTCOPLL}$	0.50	2.25	0.50	2.99	-	-	ns

Table 110. Selectable I/O Standard Output Delays

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	Min
LVCMOS		0.00		0.00		0.00	ns
LVTTL		0.00		0.00		0.00	ns
2.5 V		0.00		0.09		0.10	ns
1.8 V		2.49		2.98		3.03	ns
PCI		–0.03		0.17		0.16	ns
GTL+		0.75		0.75		0.76	ns
SSTL-3 Class I		1.39		1.51		1.50	ns
SSTL-3 Class II		1.11		1.23		1.23	ns
SSTL-2 Class I		1.35		1.48		1.47	ns
SSTL-2 Class II		1.00		1.12		1.12	ns
LVDS		–0.48		–0.48		–0.48	ns
CTT		0.00		0.00		0.00	ns
AGP		0.00		0.00		0.00	ns

Power Consumption

To estimate device power consumption, use the interactive power calculator on the Altera web site at **http://www.altera.com**.

Configuration & Operation

The APEX 20K architecture supports several configuration schemes. This section summarizes the device operating modes and available device configuration schemes.

Operating Modes

The APEX architecture uses SRAM configuration elements that require configuration data to be loaded each time the circuit powers up. The process of physically loading the SRAM data into the device is called configuration. During initialization, which occurs immediately after configuration, the device resets registers, enables I/O pins, and begins to operate as a logic device. The I/O pins are tri-stated during power-up, and before and during configuration. Together, the configuration and initialization processes are called *command mode*; normal device operation is called *user mode*.

Before and during device configuration, all I/O pins are pulled to V_{CCIO} by a built-in weak pull-up resistor.